

March 1997

**4A, 400V - 600V Ultrafast Diodes**

### Features

- Ultrafast with Soft Recovery ..... <55ns
- Operating Temperature ..... +175°C
- Reverse Voltage Up To ..... 600V
- Avalanche Energy Rated
- Planar Construction

### Applications

- Switching Power Supplies
- Power Switching Circuits
- General Purpose

### Description

RURD440, RURD450, RURD460, RURD440S, RURD450S and RURD460S (TA49035) are ultrafast diodes with soft recovery characteristics ( $t_{RR} < 55ns$ ). They have low forward voltage drop and are silicon nitride passivated ion-implanted epitaxial planar construction.

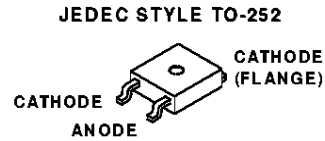
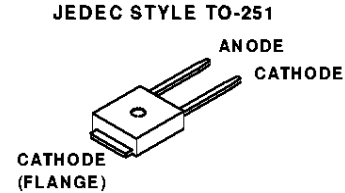
These devices are intended for use as freewheeling/clamping diodes and rectifiers in a variety of switching power supplies and other power switching applications. Their low stored charge and ultrafast soft recovery minimize ringing and electrical noise in many power switching circuits reducing power loss in the switching transistors.

#### PACKAGING AVAILABILITY

PART NUMBER	PACKAGE	BRAND
RURD440	TO-251	RUR440
RURD450	TO-251	RUR450
RURD460	TO-251	RUR460
RURD440S	TO-252	RUR440
RURD450S	TO-252	RUR450
RURD460S	TO-252	RUR460

NOTE: When ordering, use the entire part number.

### Package



### Symbol



### Absolute Maximum Ratings $T_C = +25^\circ C$ , Unless Otherwise Specified

	RURD440 RURD440S	RURD450 RURD450S	RURD460 RURD460S	UNITS
Peak Repetitive Reverse Voltage ..... $V_{RRM}$	400	500	600	V
Working Peak Reverse Voltage ..... $V_{RWM}$	400	500	600	V
DC Blocking Voltage ..... $V_R$	400	500	600	V
Average Rectified Forward Current ..... $I_{F(AV)}$ ( $T_C = +160^\circ C$ )	4	4	4	A
Repetitive Peak Surge Current ..... $I_{FSM}$ (Square Wave, 20kHz)	8	8	8	A
Nonrepetitive Peak Surge Current ..... $I_{FSM}$ (Halfwave, 1 phase, 60Hz)	40	40	40	A
Maximum Power Dissipation ..... $P_D$	50	50	50	W
Avalanche Energy ( $L = 40mH$ ) ..... $E_{AVL}$	10	10	10	mj
Operating and Storage Temperature ..... $T_{STG}, T_J$	-65 to +175	-65 to +175	-65 to +175	°C

# Specifications RURD440, RURD450, RURD460, RURD440S, RURD450S, RURD460S

## Electrical Specifications $T_C = +25^\circ\text{C}$ , Unless Otherwise Specified

SYMBOL	TEST CONDITION	LIMITS									UNITS
		RURD440, RURD440S			RURD450, RURD450S			RURD460, RURD460S			
		MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
$V_F$	$I_F = 4\text{A}, T_C = +25^\circ\text{C}$	-	-	1.5	-	-	1.5	-	-	1.5	V
$V_F$	$I_F = 4\text{A}, T_C = +150^\circ\text{C}$	-	-	1.2	-	-	1.2	-	-	1.2	V
$I_R$	$V_R = 400\text{V}, T_C = +25^\circ\text{C}$	-	-	100	-	-	-	-	-	-	$\mu\text{A}$
	$V_R = 500\text{V}, T_C = +25^\circ\text{C}$	-	-	-	-	-	100	-	-	-	$\mu\text{A}$
	$V_R = 600\text{V}, T_C = +25^\circ\text{C}$	-	-	-	-	-	-	-	-	100	$\mu\text{A}$
$I_R$	$V_R = 400\text{V}, T_C = +150^\circ\text{C}$	-	-	500	-	-	-	-	-	-	$\mu\text{A}$
	$V_R = 500\text{V}, T_C = +150^\circ\text{C}$	-	-	-	-	-	500	-	-	-	$\mu\text{A}$
	$V_R = 600\text{V}, T_C = +150^\circ\text{C}$	-	-	-	-	-	-	-	-	500	$\mu\text{A}$
$t_{RR}$	$I_F = 1\text{A}, di_F/dt = 100\text{A}/\mu\text{s}$	-	-	55	-	-	55	-	-	55	ns
	$I_F = 4\text{A}, di_F/dt = 100\text{A}/\mu\text{s}$	-	-	60	-	-	60	-	-	60	ns
$t_A$	$I_F = 4\text{A}, di_F/dt = 100\text{A}/\mu\text{s}$	-	32	-	-	32	-	-	32	-	ns
$t_B$	$I_F = 4\text{A}, di_F/dt = 100\text{A}/\mu\text{s}$	-	15	-	-	15	-	-	15	-	ns
$Q_{RR}$	$I_F = 4\text{A}, di_F/dt = 100\text{A}/\mu\text{s}$	-	50	-	-	50	-	-	50	-	nC
$C_J$	$V_R = 10\text{V}, I_F = 0\text{A}$	-	15	-	-	15	-	-	15	-	pF
$R_{\theta JC}$		-	-	3	-	-	3	-	-	3	$^\circ\text{C}/\text{W}$

### DEFINITIONS

$V_F$  = Instantaneous forward voltage ( $p_w = 300\mu\text{s}$ ,  $D = 2\%$ ).

$I_R$  = Instantaneous reverse current.

$t_{RR}$  = Reverse recovery time (See Figure 2), summation of  $t_A + t_B$ .

$t_A$  = Time to reach peak reverse current (See Figure 2).

$t_B$  = Time from peak  $I_{RM}$  to projected zero crossing of  $I_{RM}$  based on a straight line from peak  $I_{RM}$  through 25% of  $I_{RM}$  (See Figure 2).

$R_{\theta JC}$  = Thermal resistance junction to case.

$E_{AVL}$  = Controlled avalanche energy (See Figures 9 and 10).

$p_w$  = pulse width.

$D$  = duty cycle.

$V_1$  AMPLITUDE CONTROLS  $I_F$   
 $V_2$  AMPLITUDE CONTROLS  $di_F/dt$   
 $L_1$  = SELF INDUCTANCE OF  
 $R_4 + L_{LOOP}$

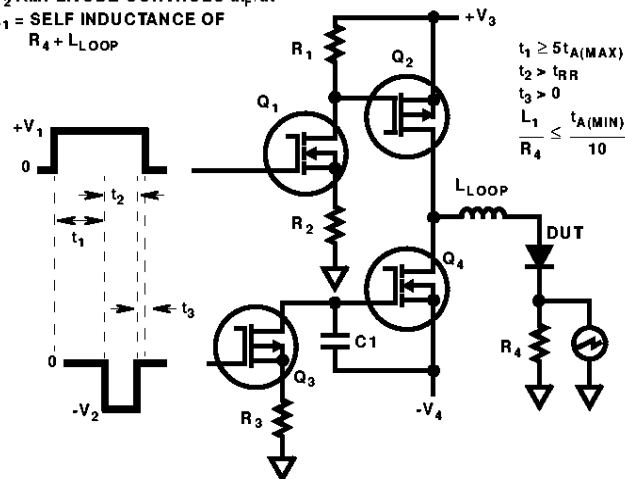


FIGURE 1.  $t_{RR}$  TEST CIRCUIT

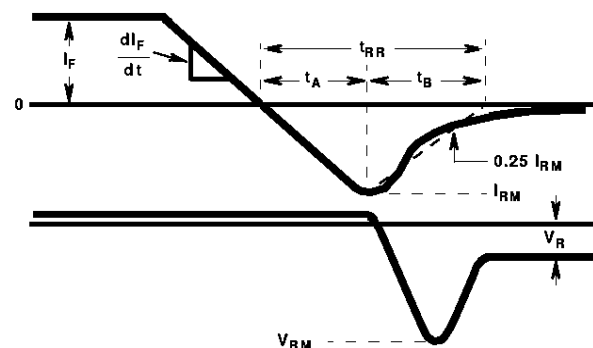


FIGURE 2.  $t_{RR}$  WAVEFORMS AND DEFINITIONS

Typical Performance Curves

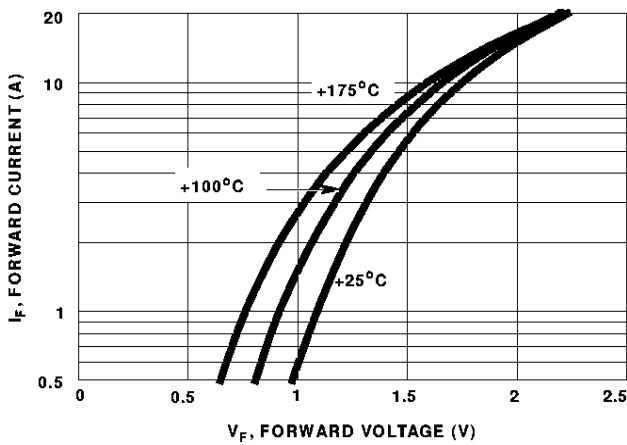


FIGURE 3. TYPICAL FORWARD CURRENT vs FORWARD VOLTAGE DROP

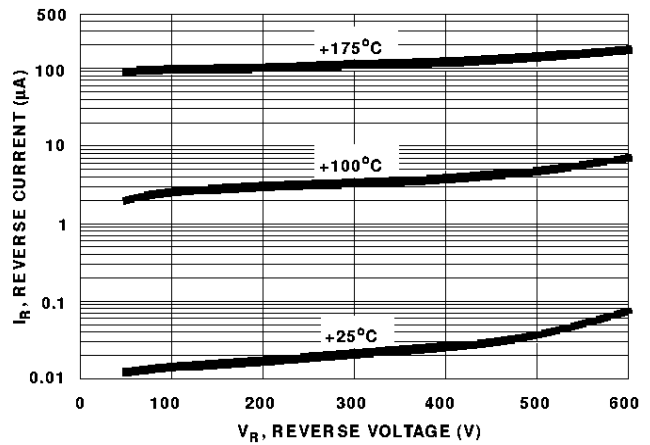


FIGURE 4. TYPICAL REVERSE CURRENT vs REVERSE VOLTAGE

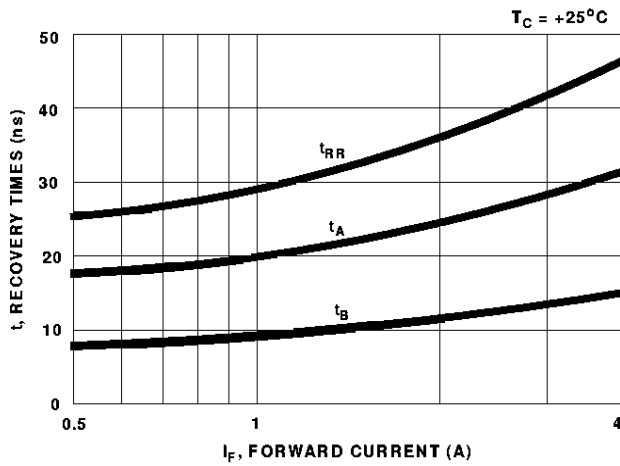


FIGURE 5. TYPICAL  $t_{RR}$ ,  $t_A$  AND  $t_B$  CURVES vs FORWARD CURRENT

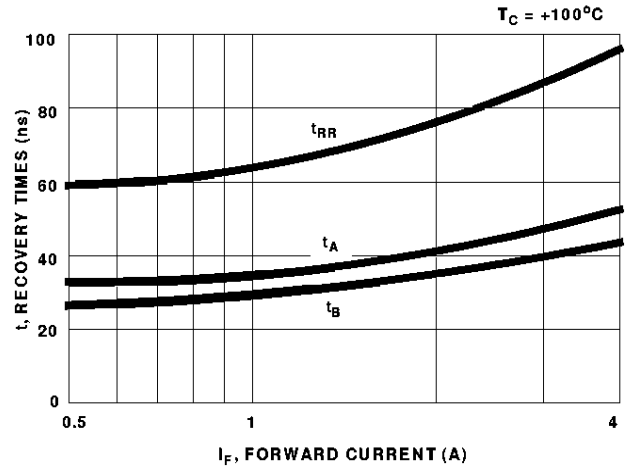


FIGURE 6. TYPICAL  $t_{RR}$ ,  $t_A$  AND  $t_B$  CURVES vs FORWARD CURRENT

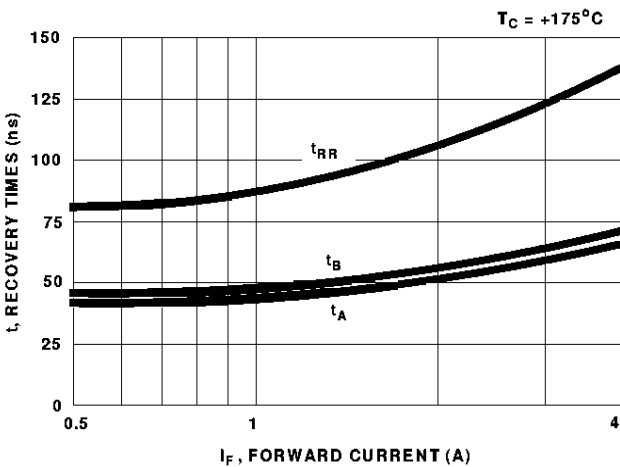


FIGURE 7. TYPICAL  $t_{RR}$ ,  $t_A$  AND  $t_B$  CURVES vs FORWARD CURRENT

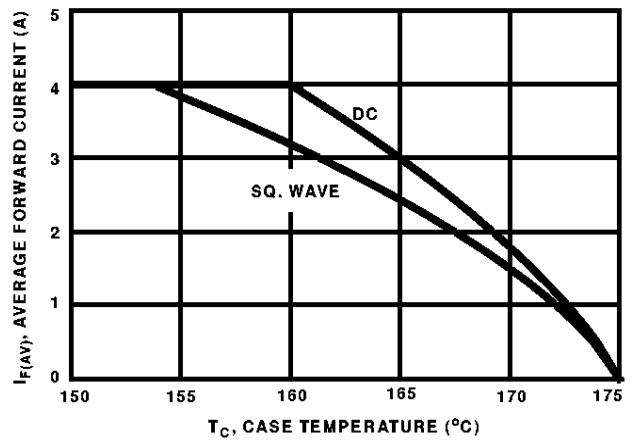


FIGURE 8. CURRENT DERATING CURVE FOR ALL TYPES

$I_{MAX} = 1A$

$L = 40mH$

$R < 0.1\Omega$

$E_{AVL} = 1/2LI^2 [V_{AVL} / (V_{AVL} - V_{DD})]$

$Q_1$  AND  $Q_2$  ARE 1000V MOSFETs

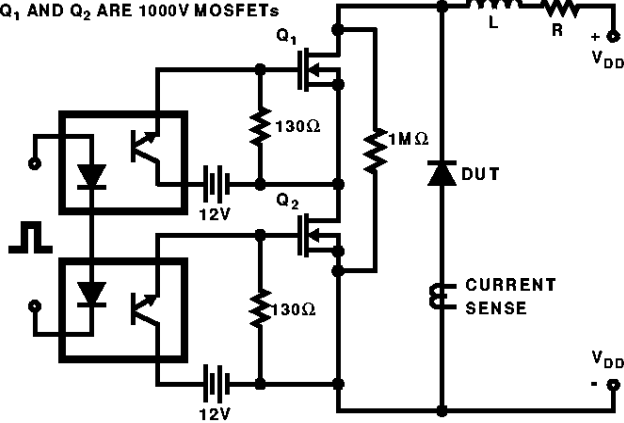


FIGURE 9. AVALANCHE ENERGY TEST CIRCUIT

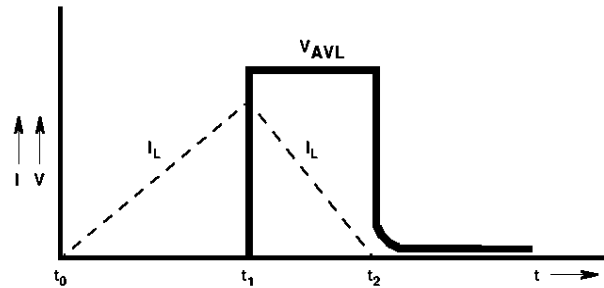


FIGURE 10. AVALANCHE CURRENT AND VOLTAGE WAVEFORMS

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